Lattice Semiconductor Corporation - LCMXO3LF-1300E-5UWG36CTR50 Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

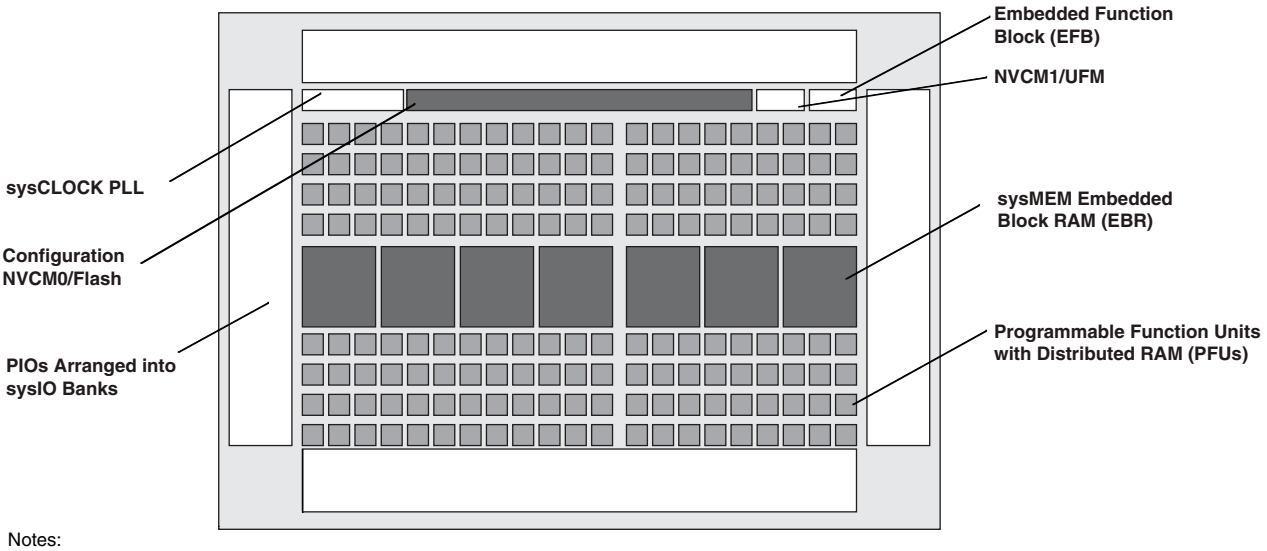
The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Discontinued at Digi-Key
Number of LABs/CLBs	160
Number of Logic Elements/Cells	1280
Total RAM Bits	65536
Number of I/O	28
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	36-UFBGA, WLCSP
Supplier Device Package	36-WLCSP (2.54x2.59)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo3lf-1300e-5uwg36ctr50

Architecture Overview

The MachXO3L/LF family architecture contains an array of logic blocks surrounded by Programmable I/O (PIO). All logic density devices in this family have sysCLOCK™ PLLs and blocks of sysMEM Embedded Block RAM (EBRs). Figure 2-1 and Figure 2-2 show the block diagrams of the various family members.

Figure 2-1. Top View of the MachXO3L/LF-1300 Device



Notes:
- MachXO3L/LF-640 is similar to MachXO3L/LF-1300. MachXO3L/LF-640 has a lower LUT count.
- MachXO3L devices have NVCM, MachXO3LF devices have Flash.

Modes of Operation

Each slice has up to four potential modes of operation: Logic, Ripple, RAM and ROM.

Logic Mode
In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note LUT8 requires more than four slices.

Ripple Mode
Ripple mode supports the efficient implementation of small arithmetic functions. In Ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/down counter with asynchronous clear
- Up/down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
  — A greater-than-or-equal-to B
  — A not-equal-to B
  — A less-than-or-equal-to B

Ripple mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per-slice basis to allow fast arithmetic functions to be constructed by concatenating slices.

RAM Mode

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed by using each LUT block in Slice 0 and Slice 1 as a 16x1-bit memory. Slice 2 is used to provide memory address and control signals.

MachXO3L/LF devices support distributed memory initialization.

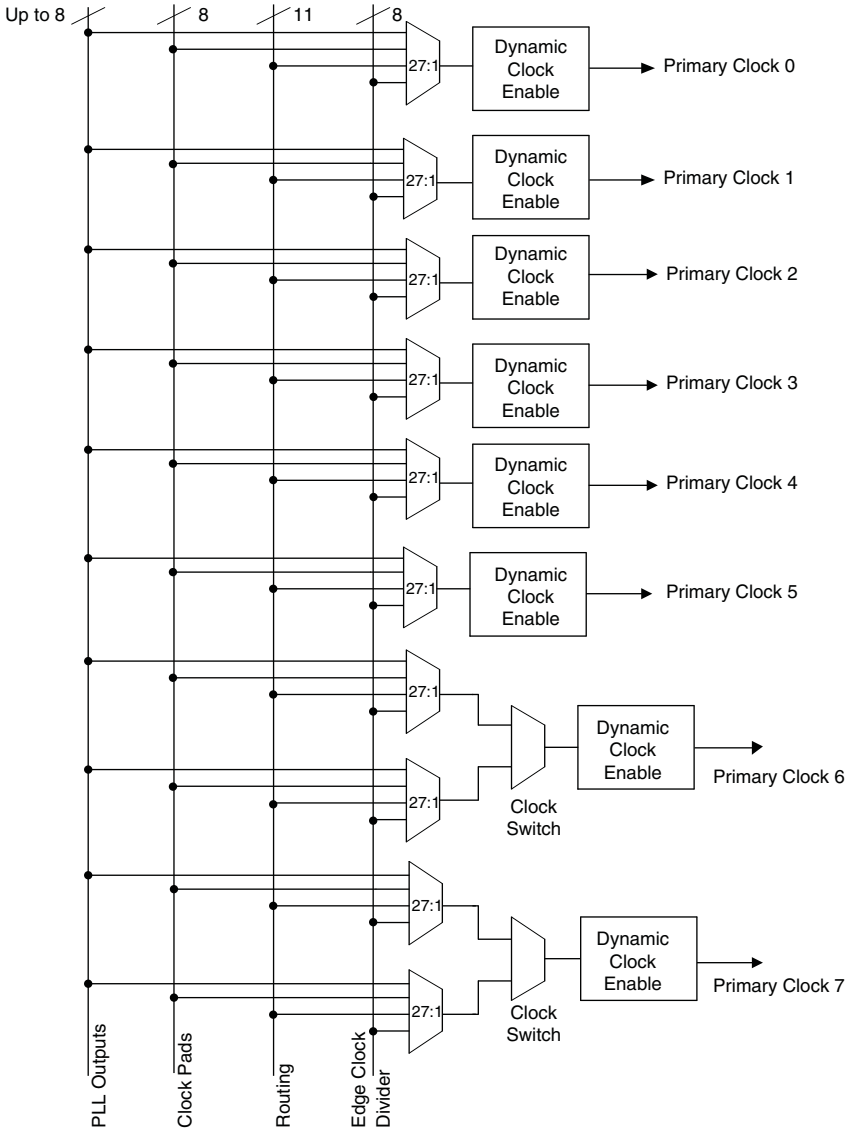
The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2-3 shows the number of slices required to implement different distributed RAM primitives. For more information about using RAM in MachXO3L/LF devices, please see TN1290, Memory Usage Guide for MachXO3 Devices.

Table 2-3. Number of Slices Required For Implementing Distributed RAM

	SPR 16x4	PDPR 16x4
Number of slices	3	3

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM

Figure 2-5. Primary Clocks for MachXO3L/LF Devices



Eight secondary high fanout nets are generated from eight 8:1 muxes as shown in Figure 2-6. One of the eight inputs to the secondary high fanout net input mux comes from dual function clock pins and the remaining seven come from internal routing. The maximum frequency for the secondary clock network is shown in MachXO3L/LF External Switching Characteristics table.

PIO

The PIO contains three blocks: an input register block, output register block and tri-state register block. These blocks contain registers for operating in a variety of modes along with the necessary clock and selection logic.

Table 2-8. PIO Signal List

Pin Name	I/O Type	Description
CE	Input	Clock Enable
D	Input	Pin input from sysIO buffer.
INDD	Output	Register bypassed input.
INCK	Output	Clock input
Q0	Output	DDR positive edge input
Q1	Output	Registered input/DDR negative edge input
D0	Input	Output signal from the core (SDR and DDR)
D1	Input	Output signal from the core (DDR)
TD	Input	Tri-state signal from the core
Q	Output	Data output signals to sysIO Buffer
TQ	Output	Tri-state output signals to sysIO Buffer
SCLK	Input	System clock for input and output/tri-state blocks.
RST	Input	Local set reset signal

Input Register Block

The input register blocks for the PIOs on all edges contain delay elements and registers that can be used to condition high-speed interface signals before they are passed to the device core.

Left, Top, Bottom Edges

Input signals are fed from the sysIO buffer to the input register block (as signal D). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), and a clock (INCK). If an input delay is desired, users can select a fixed delay. I/Os on the bottom edge also have a dynamic delay, DEL[4:0]. The delay, if selected, reduces input register hold time requirements when using a global clock. The input block allows two modes of operation. In single data rate (SDR) the data is registered with the system clock (SCLK) by one of the registers in the single data rate sync register block. In Generic DDR mode, two registers are used to sample the data on the positive and negative edges of the system clock (SCLK) signal, creating two data streams.

Hot Socketing

The MachXO3L/LF devices have been carefully designed to ensure predictable behavior during power-up and power-down. Leakage into I/O pins is controlled to within specified limits. This allows for easy integration with the rest of the system. These capabilities make the MachXO3L/LF ideal for many multiple power supply and hot-swap applications.

On-chip Oscillator

Every MachXO3L/LF device has an internal CMOS oscillator. The oscillator output can be routed as a clock to the clock tree or as a reference clock to the sysCLOCK PLL using general routing resources. The oscillator frequency can be divided by internal logic. There is a dedicated programming bit and a user input to enable/disable the oscillator. The oscillator frequency ranges from 2.08 MHz to 133 MHz. The software default value of the Master Clock (MCLK) is nominally 2.08 MHz. When a different MCLK is selected during the design process, the following sequence takes place:

1. Device powers up with a nominal MCLK frequency of 2.08 MHz.
2. During configuration, users select a different master clock frequency.
3. The MCLK frequency changes to the selected frequency once the clock configuration bits are received.
4. If the user does not select a master clock frequency, then the configuration bitstream defaults to the MCLK frequency of 2.08 MHz.

Table 2-13 lists all the available MCLK frequencies.

Table 2-13. Available MCLK Frequencies

MCLK (MHz, Nominal)	MCLK (MHz, Nominal)	MCLK (MHz, Nominal)
2.08 (default)	9.17	33.25
2.46	10.23	38
3.17	13.3	44.33
4.29	14.78	53.2
5.54	20.46	66.5
7	26.6	88.67
8.31	29.56	133

Security and One-Time Programmable Mode (OTP)

For applications where security is important, the lack of an external bitstream provides a solution that is inherently more secure than SRAM-based FPGAs. This is further enhanced by device locking. MachXO3L/LF devices contain security bits that, when set, prevent the readback of the SRAM configuration and NVCM/Flash spaces. The device can be in one of two modes:

1. Unlocked – Readback of the SRAM configuration and NVCM/Flash spaces is allowed.

2. Permanently Locked – The device is permanently locked.

Once set, the only way to clear the security bits is to erase the device. To further complement the security of the device, a One Time Programmable (OTP) mode is available. Once the device is set in this mode it is not possible to erase or re-program the NVCM/Flash and SRAM OTP portions of the device. For more details, refer to TN1279, MachXO3 Programming and Configuration Usage Guide.

Password

The MachXO3LF supports a password-based security access feature also known as Flash Protect Key. Optionally, the MachXO3L device can be ordered with a custom specification (c-spec) to support this feature. The Flash Protect Key feature provides a method of controlling access to the Configuration and Programming modes of the device. When enabled, the Configuration and Programming edit mode operations (including Write, Verify and Erase operations) are allowed only when coupled with a Flash Protect Key which matches that expected by the device. Without a valid Flash Protect Key, the user can perform only rudimentary non-configuration operations such as Read Device ID. For more details, refer to TN1313, Using Password Security with MachXO3 Devices.

Dual Boot

MachXO3L/LF devices can optionally boot from two patterns, a primary bitstream and a golden bitstream. If the primary bitstream is found to be corrupt while being downloaded into the SRAM, the device shall then automatically re-boot from the golden bitstream. Note that the primary bitstream must reside in the external SPI Flash. The golden image MUST reside in an on-chip NVCM/Flash. For more details, refer to TN1279, MachXO3 Programming and Configuration Usage Guide.

Soft Error Detection

The SED feature is a CRC check of the SRAM cells after the device is configured. This check ensures that the SRAM cells were configured successfully. This feature is enabled by a configuration bit option. The Soft Error Detection can also be initiated in user mode via an input to the fabric. The clock for the Soft Error Detection circuit is generated using a dedicated divider. The undivided clock from the on-chip oscillator is the input to this divider. For low power applications users can switch off the Soft Error Detection circuit. For more details, refer to TN1292, MachXO3 Soft Error Detection Usage Guide.

Soft Error Correction

The MachXO3LF device supports Soft Error Correction (SEC). Optionally, the MachXO3L device can be ordered with a custom specification (c-spec) to support this feature. When BACKGROUND_RECONFIG is enabled using the Lattice Diamond Software in a design, asserting the PROGRAMN pin or issuing the REFRESH sysConfig command refreshes the SRAM array from configuration memory. Only the detected error bit is corrected. No other SRAM cells are changed, allowing the user design to function uninterrupted.

During the project design phase, if the overall system cannot guarantee containment of the error or its subsequent effects on downstream data or control paths, Lattice recommends using SED only. The MachXO3 can be then be soft-reset by asserting PROGRAMN or issuing the Refresh command over a sysConfig port in response to SED. Soft-reset additionally erases the SRAM array prior to the SRAM refresh, and asserts internal Reset circuitry to guarantee a known state. For more details, refer to TN1292, MachXO3 Soft Error Detection (SED)/Correction (SEC) Usage Guide.

Power-On-Reset Voltage Levels[1, 2, 3, 4, 5]

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{PORUP}	Power-On-Reset ramp up trip point (band gap based circuit monitoring V_{CCINT} and V_{CCIO0})	0.9	—	1.06	V
$V_{PORUPEXT}$	Power-On-Reset ramp up trip point (band gap based circuit monitoring external V_{CC} power supply)	1.5	—	2.1	V
$V_{PORDNBG}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CCINT})	0.75	—	0.93	V
$V_{PORDNBGEXT}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CC})	0.98	—	1.33	V
$V_{PORDNSRAM}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CCINT})	—	0.6	—	V
$V_{PORDNSRAMEXT}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CC})	—	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
2. For devices without voltage regulators V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage.
3. Note that V_{PORUP} (min.) and $V_{PORDNBG}$ (max.) are in different process corners. For any given process corner $V_{PORDNBG}$ (max.) is always 12.0 mV below V_{PORUP} (min.).
4. $V_{PORUPEXT}$ is for C devices only. In these devices a separate POR circuit monitors the external V_{CC} power supply.
5. V_{CCIO0} does not have a Power-On-Reset ramp down trip point. V_{CCIO0} must remain within the Recommended Operating Conditions to ensure proper operation.

Hot Socketing Specifications[1, 2, 3]

Symbol	Parameter	Condition	Max.	Units
I_{DK}	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/-1000	µA

1. Insensitive to sequence of V_{CC} and V_{CCIO}. However, assumes monotonic rise/fall rates for V_{CC} and V_{CCIO}.
2. $0 < V_{CC} < V_{CC}$ (MAX), $0 < V_{CCIO} < V_{CCIO}$ (MAX).
3. I_{DK} is additive to I_{PU}, I_{PD} or I_{BH}.

ESD Performance

Please refer to the MachXO2 Product Family Qualification Summary for complete qualification data, including ESD performance.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
I_{IL}, I_{IH}[1, 4]	Input or I/O Leakage	Clamp OFF and $V_{CCIO} < V_{IN} < V_{IH}$ (MAX)	—	—	+175	µA
		Clamp OFF and $V_{IN} = V_{CCIO}$	–10	—	10	µA
		Clamp OFF and V_{CCIO} - 0.97 V < V_{IN} < V_{CCIO}	–175	—	—	µA
		Clamp OFF and 0 V < V_{IN} < V_{CCIO} - 0.97 V	—	—	10	µA
		Clamp OFF and V_{IN} = GND	—	—	10	µA
		Clamp ON and 0 V < $V_{IN} < V_{CCIO}$	—	—	10	µA
I_{PU}	I/O Active Pull-up Current	0 < V_{IN} < 0.7 V_{CCIO}	–30	—	–309	µA
I_{PD}	I/O Active Pull-down Current	V_{IL} (MAX) < $V_{IN} < V_{CCIO}$	30	—	305	µA
I_{BHLS}	Bus Hold Low sustaining current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	µA
I_{BHHS}	Bus Hold High sustaining current	$V_{IN} = 0.7V_{CCIO}$	–30	—	—	µA
I_{BHLO}	Bus Hold Low Overdrive current	0 ≤ V_{IN} ≤ V_{CCIO}	—	—	305	µA
I_{BHHO}	Bus Hold High Overdrive current	0 ≤ V_{IN} ≤ V_{CCIO}	—	—	–309	µA
V_{BHT}[3]	Bus Hold Trip Points		V_{IL} (MAX)	—	V_{IH} (MIN)	V
C1	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5	9	pf
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5.5	7	pf
V_{HYST}	Hysteresis for Schmitt Trigger Inputs[5]	V_{CCIO} = 3.3 V, Hysteresis = Large	—	450	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Large	—	250	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Large	—	125	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Large	—	100	—	mV
		V_{CCIO} = 3.3 V, Hysteresis = Small	—	250	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Small	—	150	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Small	—	60	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Small	—	40	—	mV

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25 °C, f = 1.0 MHz.
3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.
4. When V_{IH} is higher than V_{CCIO}, a transient current typically of 30 ns in duration or less with a peak current of 6mA can occur on the high-to-low transition. For true LVDS output pins in MachXO3L/LF devices, V_{IH} must be less than or equal to V_{CCIO}.
5. With bus keeper circuit turned on. For more details, refer to TN1280, MachXO3 sysIO Usage Guide.

Programming and Erase Supply Current – C/E Devices[1, 2, 3, 4]

Symbol	Parameter	Device	Typ.[4]	Units
I_{CC}	Core Power Supply	LCMXO3L/LF-1300C 256 Ball Package	22.1	mA
		LCMXO3L/LF-2100C	22.1	mA
		LCMXO3L/LF-2100C 324 Ball Package	26.8	mA
		LCMXO3L/LF-4300C	26.8	mA
		LCMXO3L/LF-4300C 400 Ball Package	33.2	mA
		LCMXO3L/LF-6900C	33.2	mA
		LCMXO3L/LF-9400C	39.6	mA
		LCMXO3L/LF-640E	17.7	mA
		LCMXO3L/LF-1300E	17.7	mA
		LCMXO3L/LF-1300E 256 Ball Package	18.3	mA
		LCMXO3L/LF-2100E	18.3	mA
		LCMXO3L/LF-2100E 324 Ball Package	20.4	mA
		LCMXO3L/LF-4300E	20.4	mA
		LCMXO3L/LF-6900E	23.9	mA
		LCMXO3L/LF-9400E	28.5	mA
I_{CCIO}	Bank Power Supply[5] VCCIO = 2.5 V	All devices	0	mA

1. For further information on supply current, please refer to TN1289, Power Estimation and Management for MachXO3 Devices.
2. Assumes all inputs are held at V_{CCIO} or GND and all outputs are tri-stated.
3. Typical user pattern.
4. JTAG programming is at 25 MHz.
5. T_J = 25 °C, power supplies at nominal voltage.
6. Per bank. V_{CCIO} = 2.5 V. Does not include pull-up/pull-down.

BLVDS

The MachXO3L/LF family supports the BLVDS standard through emulation. The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs. The input standard is supported by the LVDS differential input buffer. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.

Figure 3-2. BLVDS Multi-point Output Example

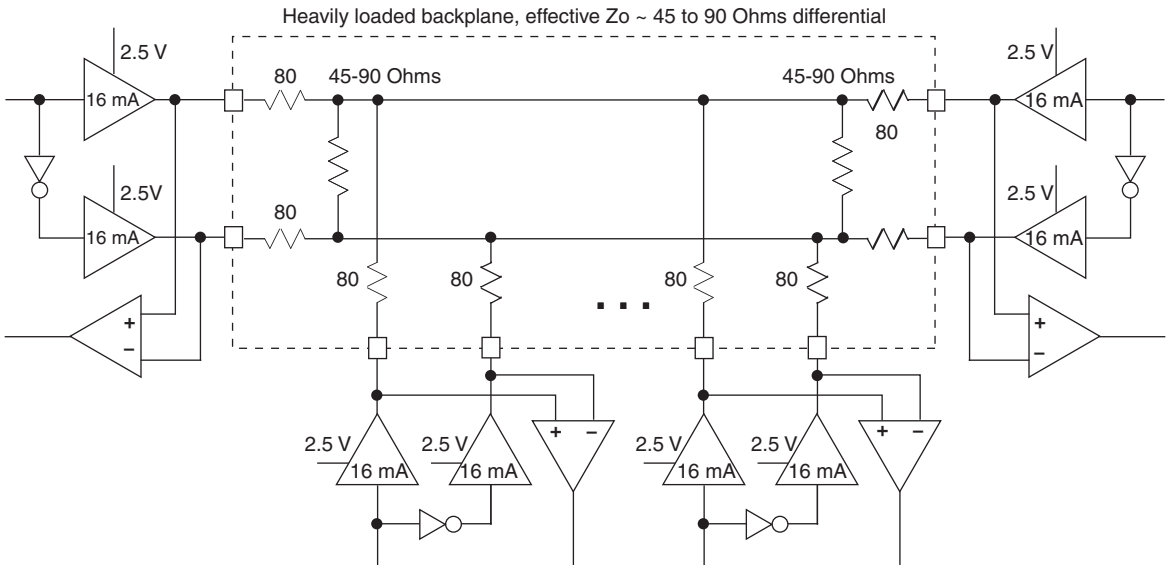


Table 3-2. BLVDS DC Conditions[1]

Over Recommended Operating Conditions

Symbol	Description	Nominal		Units
		Zo = 45	Zo = 90	
Z_{OUT}	Output impedance	20	20	Ohms
R_S	Driver series resistance	80	80	Ohms
R_{TLEFT}	Left end termination	45	90	Ohms
R_{TRIGHT}	Right end termination	45	90	Ohms
V_{OH}	Output high voltage	1.376	1.480	V
V_{OL}	Output low voltage	1.124	1.020	V
V_{OD}	Output differential voltage	0.253	0.459	V
V_{CM}	Output common mode voltage	1.250	1.250	V
I_{DC}	DC output current	11.236	10.204	mA

1. For input buffer, see LVDS table.

MIPI D-PHY Emulation

MachXO3L/LF devices can support MIPI D-PHY unidirectional HS (High Speed) and bidirectional LP (Low Power) inputs and outputs via emulation. In conjunction with external resistors High Speed IOs use the LVDS25E buffer and Low Power IOs use the LVCMOS buffers. The scheme shown in Figure 3-4 is one possible solution for MIPI D-PHY Receiver implementation. The scheme shown in Figure 3-5 is one possible solution for MIPI D-PHY Transmitter implementation.

Figure 3-4. MIPI D-PHY Input Using External Resistors

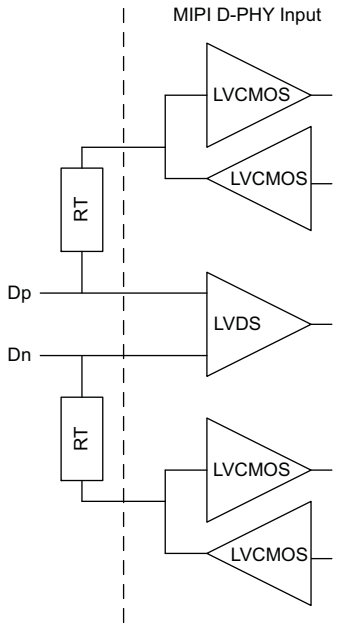


Table 3-4. MIPI DC Conditions[1]

	Description	Min.	Typ.	Max.	Units
Receiver					
External Termination					
RT	1% external resistor with VCCIO=2.5 V	—	50	—	Ohms
	1% external resistor with VCCIO=3.3 V	—	50	—	Ohms
High Speed					
VCCIO	VCCIO of the Bank with LVDS Emulated input buffer	—	2.5	—	V
	VCCIO of the Bank with LVDS Emulated input buffer	—	3.3	—	V
VCMRX	Common-mode voltage HS receive mode	150	200	250	mV
VIDTH	Differential input high threshold	—	—	100	mV
VIDTL	Differential input low threshold	–100	—	—	mV
VIHHS	Single-ended input high voltage	—	—	300	mV
VILHS	Single-ended input low voltage	100	—	—	mV
ZID	Differential input impedance	80	100	120	Ohms

Typical Building Block Function Performance – C/E Devices[1]

Pin-to-Pin Performance (LVCMOS25 12 mA Drive)

Function	–6 Timing	Units
Basic Functions		
16-bit decoder	8.9	ns
4:1 MUX	7.5	ns
16:1 MUX	8.3	ns

Register-to-Register Performance

Function	–6 Timing	Units
Basic Functions		
16:1 MUX	412	MHz
16-bit adder	297	MHz
16-bit counter	324	MHz
64-bit counter	161	MHz
Embedded Memory Functions		
1024x9 True-Dual Port RAM (Write Through or Normal, EBR output registers)	183	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (one PFU)	500	MHz

1. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.

Derating Logic Timing

Logic timing provided in the following sections of the data sheet and the Lattice design tools are worst case numbers in the operating range. Actual delays may be much faster. Lattice design tools can provide logic timing numbers at a particular temperature and voltage.

Parameter	Description	Device	–6		–5		Units
			Min.	Max.	Min.	Max.	
Generic DDRX1 Inputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX1_RX.SCLK.Aligned[8, 9]							
t_{DVA}	Input Data Valid After CLK	All MachXO3L/LF devices, all sides	—	0.317	—	0.344	UI
t_{DVE}	Input Data Hold After CLK		0.742	—	0.702	—	UI
f_{DATA}	DDRX1 Input Data Speed		—	300	—	250	Mbps
f_{DDRX1}	DDRX1 SCLK Frequency		—	150	—	125	MHz
Generic DDRX1 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX1_RX.SCLK.Centered[8, 9]							
t_{SU}	Input Data Setup Before CLK	All MachXO3L/LF devices, all sides	0.566	—	0.560	—	ns
t_{HO}	Input Data Hold After CLK		0.778	—	0.879	—	ns
f_{DATA}	DDRX1 Input Data Speed		—	300	—		Mbps
f_{DDRX1}	DDRX1 SCLK Frequency		—	150	—	125	MHz
Generic DDRX2 Inputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX2_RX.ECLK.Aligned[8, 9]							
t_{DVA}	Input Data Valid After CLK	MachXO3L/LF devices, bottom side only	—	0.316	—	0.342	UI
t_{DVE}	Input Data Hold After CLK		0.710	—	0.675	—	UI
f_{DATA}	DDRX2 Serial Input Data Speed		—	664	—	554	Mbps
f_{DDRX2}	DDRX2 ECLK Frequency		—	332	—	277	MHz
f_{SCLK}	SCLK Frequency		—	166	—	139	MHz
Generic DDRX2 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX2_RX.ECLK.Centered[8, 9]							
t_{SU}	Input Data Setup Before CLK	MachXO3L/LF devices, bottom side only	0.233	—	0.219	—	ns
t_{HO}	Input Data Hold After CLK		0.287	—	0.287	—	ns
f_{DATA}	DDRX2 Serial Input Data Speed		—	664	—	554	Mbps
f_{DDRX2}	DDRX2 ECLK Frequency		—	332	—	277	MHz
f_{SCLK}	SCLK Frequency		—	166	—	139	MHz
Generic DDR4 Inputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX4_RX.ECLK.Aligned[8]							
t_{DVA}	Input Data Valid After ECLK	MachXO3L/LF devices, bottom side only	—	0.307	—	0.320	UI
t_{DVE}	Input Data Hold After ECLK		0.782	—	0.699	—	UI
f_{DATA}	DDRX4 Serial Input Data Speed		—	800	—	630	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	400	—	315	MHz
f_{SCLK}	SCLK Frequency		—	100	—	79	MHz
Generic DDR4 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX4_RX.ECLK.Centered[8]							
t_{SU}	Input Data Setup Before ECLK	MachXO3L/LF devices, bottom side only	0.233	—	0.219	—	ns
t_{HO}	Input Data Hold After ECLK		0.287	—	0.287	—	ns
f_{DATA}	DDRX4 Serial Input Data Speed		—	800	—	630	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	400	—	315	MHz
f_{SCLK}	SCLK Frequency		—	100	—	79	MHz
7:1 LVDS Inputs (GDDR71_RX.ECLK.7:1)[9]							
t_{DVA}	Input Data Valid After ECLK	MachXO3L/LF devices, bottom side only	—	0.290	—	0.320	UI
t_{DVE}	Input Data Hold After ECLK		0.739	—	0.699	—	UI
f_{DATA}	DDR71 Serial Input Data Speed		—	756	—	630	Mbps
f_{DDR71}	DDR71 ECLK Frequency		—	378	—	315	MHz
f_{CLKIN}	7:1 Input Clock Frequency (SCLK) (minimum limited by PLL)		—	108	—	90	MHz

Figure 3-6. Receiver GDDR71_RX. Waveforms

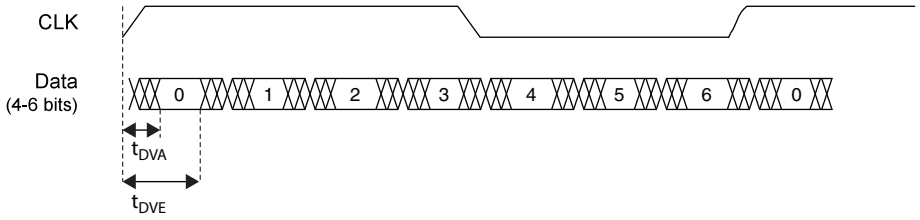
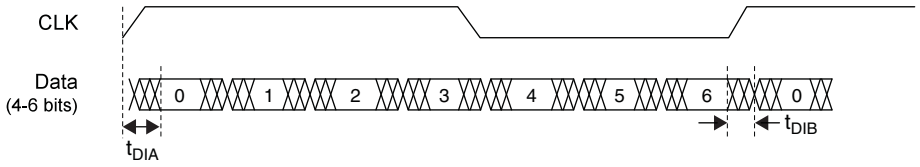


Figure 3-7. Transmitter GDDR71_TX. Waveforms



NVCM/Flash Download Time[1, 2]

Symbol	Parameter	Device	Typ.	Units
$t_{REFRESH}$	POR to Device I/O Active	LCMXO3L/LF-640	1.9	ms
		LCMXO3L/LF-1300	1.9	ms
		LCMXO3L/LF-1300 256-Ball Package	1.4	ms
		LCMXO3L/LF-2100	1.4	ms
		LCMXO3L/LF-2100 324-Ball Package	2.4	ms
		LCMXO3L/LF-4300	2.4	ms
		LCMXO3L/LF-4300 400-Ball Package	3.8	ms
		LCMXO3L/LF-6900	3.8	ms
		LCMXO3L/LF-9400C	5.2	ms

1. Assumes sysMEM EBR initialized to an all zero pattern if they are used.
2. The NVCM/Flash download time is measured starting from the maximum voltage of POR trip point.

sysCONFIG Port Timing Specifications

Symbol	Parameter		Min.	Max.	Units
All Configuration Modes					
t_{PRGM}	PROGRAMN low pulse accept		55	—	ns
t_{PRGMJ}	PROGRAMN low pulse rejection		—	25	ns
t_{INITL}	INITN low time	LCMXO3L/LF-640/ LCMXO3L/LF-1300	—	55	us
		LCMXO3L/LF-1300 256-Ball Package/ LCMXO3L/LF-2100	—	70	us
		LCMXO3L/LF-2100 324-Ball Package/ LCMXO3-4300	—	105	us
		LCMXO3L/LF-4300 400-Ball Package/ LCMXO3-6900	—	130	us
		LCMXO3L/LF-9400C	—	175	us
$t_{DPPINIT}$	PROGRAMN low to INITN low		—	150	ns
$t_{DPPDONE}$	PROGRAMN low to DONE low		—	150	ns
t_{IODISS}	PROGRAMN low to I/O disable		—	120	ns
Slave SPI					
f_{MAX}	CCLK clock frequency		—	66	MHz
t_{CCLKH}	CCLK clock pulse width high		7.5	—	ns
t_{CCLKL}	CCLK clock pulse width low		7.5	—	ns
t_{STSU}	CCLK setup time		2	—	ns
t_{STH}	CCLK hold time		0	—	ns
t_{STCO}	CCLK falling edge to valid output		—	10	ns
t_{STOZ}	CCLK falling edge to valid disable		—	10	ns
t_{STOV}	CCLK falling edge to valid enable		—	10	ns
t_{SCS}	Chip select high time		25	—	ns
t_{SCSS}	Chip select setup time		3	—	ns
t_{SCSH}	Chip select hold time		3	—	ns
Master SPI					
f_{MAX}	MCLK clock frequency		—	133	MHz
t_{MCLKH}	MCLK clock pulse width high		3.75	—	ns
t_{MCLKL}	MCLK clock pulse width low		3.75	—	ns
t_{STSU}	MCLK setup time		5	—	ns
t_{STH}	MCLK hold time		1	—	ns
t_{CSSPI}	INITN high to chip select low		100	200	ns
t_{MCLK}	INITN high to first MCLK edge		0.75	1	us

Pin Information Summary

	MachXO3L/LF -640	MachXO3L/LF-1300			
	CSFBGA121	WLCSP36	CSFBGA121	CSFBGA256	CABGA256
General Purpose IO per Bank					
Bank 0	24	15	24	50	50
Bank 1	26	0	26	52	52
Bank 2	26	9	26	52	52
Bank 3	24	4	24	16	16
Bank 4	0	0	0	16	16
Bank 5	0	0	0	20	20
Total General Purpose Single Ended IO	100	28	100	206	206
Differential IO per Bank					
Bank 0	12	8	12	25	25
Bank 1	13	0	13	26	26
Bank 2	13	4	13	26	26
Bank 3	11	2	11	8	8
Bank 4	0	0	0	8	8
Bank 5	0	0	0	10	10
Total General Purpose Differential IO	49	14	49	103	103
Dual Function IO	33	25	33	33	33
Number 7:1 or 8:1 Gearboxes					
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	7	3	7	14	14
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	7	2	7	14	14
High-speed Differential Outputs					
Bank 0	7	3	7	14	14
VCCIO Pins					
Bank 0	1	1	1	4	4
Bank 1	1	0	1	3	4
Bank 2	1	1	1	4	4
Bank 3	3	1	3	2	1
Bank 4	0	0	0	2	2
Bank 5	0	0	0	2	1
VCC	4	2	4	8	8
GND	10	2	10	24	24
NC	0	0	0	0	1
Reserved for Configuration	1	1	1	1	1
Total Count of Bonded Pins	**121**	**36**	**121**	**256**	**256**

	MachXO3L/LF-9400C			
	CSFBGA256	CABGA256	CABGA400	CABGA484
General Purpose IO per Bank				
Bank 0	50	50	83	95
Bank 1	52	52	84	96
Bank 2	52	52	84	96
Bank 3	16	16	28	36
Bank 4	16	16	24	24
Bank 5	20	20	32	36
Total General Purpose Single Ended IO	206	206	335	383
Differential IO per Bank				
Bank 0	25	25	42	48
Bank 1	26	26	42	48
Bank 2	26	26	42	48
Bank 3	8	8	14	18
Bank 4	8	8	12	12
Bank 5	10	10	16	18
Total General Purpose Differential IO	103	103	168	192
Dual Function IO	37	37	37	45
Number 7:1 or 8:1 Gearboxes				
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	20	20	22	24
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	20	20	22	24
High-speed Differential Outputs				
Bank 0	20	20	21	24
VCCIO Pins				
Bank 0	4	4	5	9
Bank 1	3	4	5	9
Bank 2	4	4	5	9
Bank 3	2	1	2	3
Bank 4	2	2	2	3
Bank 5	2	1	2	3
VCC	8	8	10	12
GND	24	24	33	52
NC	0	1	0	0
Reserved for Configuration	1	1	1	1
Total Count of Bonded Pins	**256**	**256**	**400**	**484**

MachXO3L Ultra Low Power Commercial and Industrial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-640E-5MG121C	640	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3L-640E-6MG121C	640	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3L-640E-5MG121I	640	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3L-640E-6MG121I	640	1.2 V	6	Halogen-Free csfBGA	121	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-1300E-5UWG36CTR	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3L-1300E-5UWG36CTR50	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3L-1300E-5UWG36CTR1K	1300	1.2 V	5	Halogen-Free WLCSP	36	COM
LCMXO3L-1300E-5UWG36ITR	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3L-1300E-5UWG36ITR50	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3L-1300E-5UWG36ITR1K	1300	1.2 V	5	Halogen-Free WLCSP	36	IND
LCMXO3L-1300E-5MG121C	1300	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3L-1300E-6MG121C	1300	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3L-1300E-5MG121I	1300	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3L-1300E-6MG121I	1300	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3L-1300E-5MG256C	1300	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3L-1300E-6MG256C	1300	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3L-1300E-5MG256I	1300	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3L-1300E-6MG256I	1300	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3L-1300C-5BG256C	1300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3L-1300C-6BG256C	1300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3L-1300C-5BG256I	1300	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3L-1300C-6BG256I	1300	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-2100E-5UWG49CTR	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3L-2100E-5UWG49CTR50	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3L-2100E-5UWG49CTR1K	2100	1.2 V	5	Halogen-Free WLCSP	49	COM
LCMXO3L-2100E-5UWG49ITR	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3L-2100E-5UWG49ITR50	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3L-2100E-5UWG49ITR1K	2100	1.2 V	5	Halogen-Free WLCSP	49	IND
LCMXO3L-2100E-5MG121C	2100	1.2 V	5	Halogen-Free csfBGA	121	COM
LCMXO3L-2100E-6MG121C	2100	1.2 V	6	Halogen-Free csfBGA	121	COM
LCMXO3L-2100E-5MG121I	2100	1.2 V	5	Halogen-Free csfBGA	121	IND
LCMXO3L-2100E-6MG121I	2100	1.2 V	6	Halogen-Free csfBGA	121	IND
LCMXO3L-2100E-5MG256C	2100	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3L-2100E-6MG256C	2100	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3L-2100E-5MG256I	2100	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3L-2100E-6MG256I	2100	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3L-2100E-5MG324C	2100	1.2 V	5	Halogen-Free csfBGA	324	COM
LCMXO3L-2100E-6MG324C	2100	1.2 V	6	Halogen-Free csfBGA	324	COM
LCMXO3L-2100E-5MG324I	2100	1.2 V	5	Halogen-Free csfBGA	324	IND

Date	Version	Section	Change Summary
September 2015	1.5	DC and Switching Characteristics	Updated the MIPI D-PHY Emulation section. Revised Table 3-5, MIPI D-PHY Output DC Conditions. — Revised RL Typ. value. — Revised RH description and values.
			Updated the Maximum sysIO Buffer Performance section. Revised MIPI Max. Speed value.
			Updated the MachXO3L/LF External Switching Characteristics – C/E Devices section. Added footnotes 14 and 15.
August 2015	1.4	Architecture	Updated the Device Configuration section. Added JTAGENB to TAP dual purpose pins.
		Ordering Information	Updated the top side markings section to indicate the use of LMXO3LF for the LCMXO3LF device.
March 2015	1.3	All	General update. Added MachXO3LF devices.
October 2014	1.2	Introduction	Updated Table 1-1, MachXO3L Family Selection Guide. Revised XO3L-2100 and XO3L-4300 IO for 324-ball csfBGA package.
		Architecture	Updated the Dual Boot section. Corrected information on where the primary bitstream and the golden image must reside.
		Pinout Information	Updated the Pin Information Summary section. Changed General Purpose IO Bank 5 values for MachXO3L-2100 and MachXO3L-4300 CSFBGA 324 package. Changed Number 7:1 or 8:1 Gearboxes for MachXO3L-640 and MachXO3L-1300. Removed DQS Groups (Bank 1) section. Changed VCCIO Pins Bank 1 values for MachXO3L-1300, MachXO3L-2100, MachXO3L-4300 and MachXO3L-6900 CSFBGA 256 package. Changed GND values for MachXO3L-1300, MachXO3L-2100, MachXO3L-4300 and MachXO3L-6900 CSFBGA 256 package. Changed NC values for MachXO3L-2100 and MachXO3L-4300 CSFBGA 324 package.
		DC and Switching Characteristics	Updated the BLVDS section. Changed output impedance nominal values in Table 3-2, BLVDS DC Condition.
			Updated the LVPECL section. Changed output impedance nominal value in Table 3-3, LVPECL DC Condition.
			Updated the sysCONFIG Port Timing Specifications section. Updated INITN low time values.
July 2014	1.1	DC and Switching Characteristics	Updated the Static Supply Current – C/E Devices section. Added devices.
			Updated the Programming and Erase Supply Current – C/E Device section. Added devices.
			Updated the sysIO Single-Ended DC Electrical Characteristics section. Revised footnote 4.
			Added the NVCM Download Time section.
			Updated the Typical Building Block Function Performance – C/E Devices section. Added information to footnote.
		Pinout Information	Updated the Pin Information Summary section.
		Ordering Information	Updated the MachXO3L Part Number Description section. Added packages.
			Updated the Ordering Information section. General update.